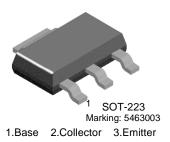


## **SB29003**

## **High Voltage Transistor**



## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	300	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> = 25°C)	2	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100\mu A, I_B = 0$	500		V
BV <sub>CER</sub>	Collector-Emitter Breakdown Voltage *	$I_{C} = 1 \text{mA}, I_{B} = 0$	400		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 400V, I <sub>E</sub> = 0		0.1	μΑ
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CE</sub> = 400V, I <sub>B</sub> = 0		0.5	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0		0.1	μΑ
h <sub>FE</sub>	DC Current Gain *	$V_{CE} = 10V, I_{C} = 1mA$ $V_{CE} = 10V, I_{C} = 10mA$ $V_{CE} = 10V, I_{C} = 50mA$ $V_{CE} = 10V, I_{C} = 100mA$	40 50 45 40	200	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	$I_{C} = 1 \text{mA}, I_{B} = 0.1 \text{mA}$ $I_{C} = 10 \text{mA}, I_{B} = 1 \text{mA}$ $I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}$		0.4 0.5 0.75	V V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage *	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA		0.75	V
C <sub>ob</sub>	Output Capatitance	V <sub>CB</sub> = 20V, I <sub>E</sub> = 0, f = 1MHz		7	pF

<sup>\*</sup> Pulse Test: PW  $\leq 300 \mu s, \ Duty \ Cycle \leq 2\%$ 

## **Typical Performance Characteristics**

Figure 1. DC Current Gain

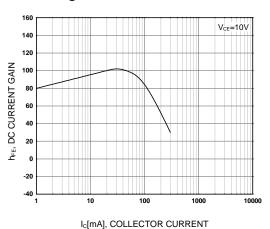


Figure 3. On Voltage

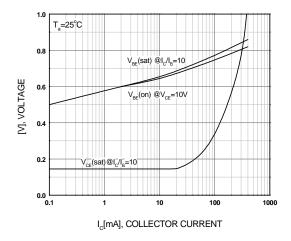


Figure 5. High Frequency Current Gain

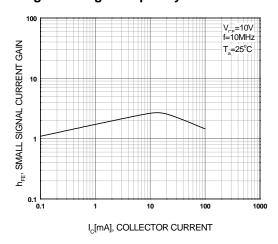


Figure 2. Capacitance

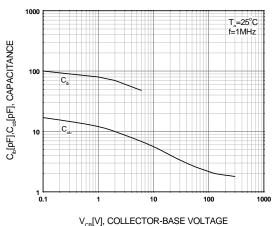
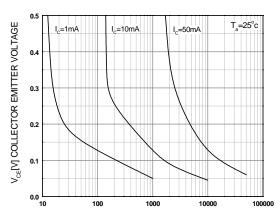


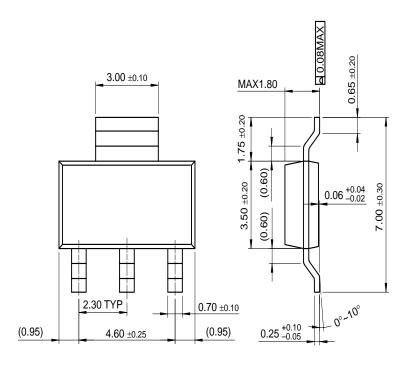
Figure 4. Collector Saturation Region

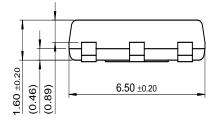


 $I_{c}[mA]$ , COLLECTOR CURRENT

### **Mechanical Dimensions**

# **SOT-223**





Dimensions in Millimeters

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